

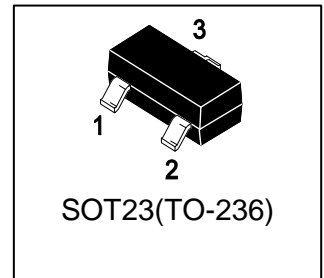
LBAS21LT1G

S-LBAS21LT1G

High Voltage Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. DEVICE MARKING AND RESISTOR VALUES

| Device | Marking | Shipping |
|------------|---------|-----------------|
| LBAS21LT1G | JS | 3000/Tape&Reel |
| LBAS21LT3G | JS | 10000/Tape&Reel |

3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|----------------------------|--------|--------|------|
| Continuous Reverse Voltage | VR | 250 | V |
| Peak Forward Current | IF | 225 | mA |
| Peak Forward Surge Current | IFSM | 625 | mA |

4. THERMAL CHARACTERISTICS

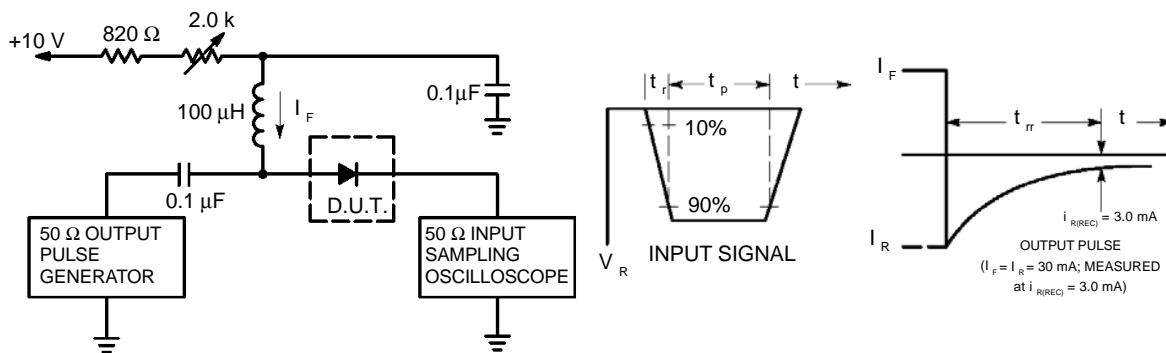
| Parameter | Symbol | Limits | Unit |
|---|-----------|----------|-------|
| Total Device Dissipation FR-5 Board, (Note 1) TA = 25°C | PD | 225 | mW |
| Derate above 25°C | | 1.8 | mW/°C |
| Thermal Resistance, Junction to Ambient | RθJA | 556 | °C/W |
| Total Device Dissipation Alumina Substrate, (Note 2) TA = 25°C | PD | 300 | mW |
| Derate above 25°C | | 2.4 | mW/°C |
| Thermal Resistance, Junction to Ambient | RθJA | 417 | °C/W |
| Junction and Storage Temperature | TJ , Tstg | -55~+150 | °C |

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

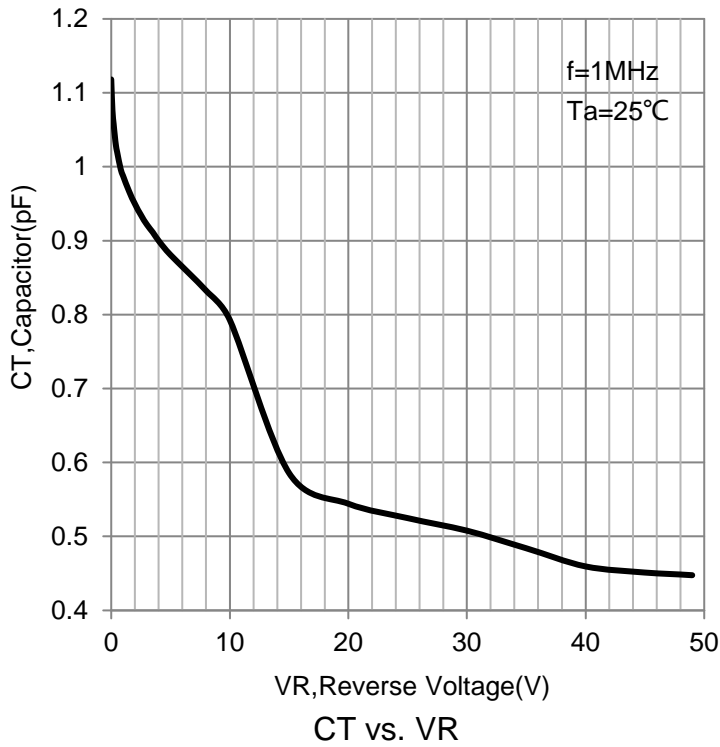
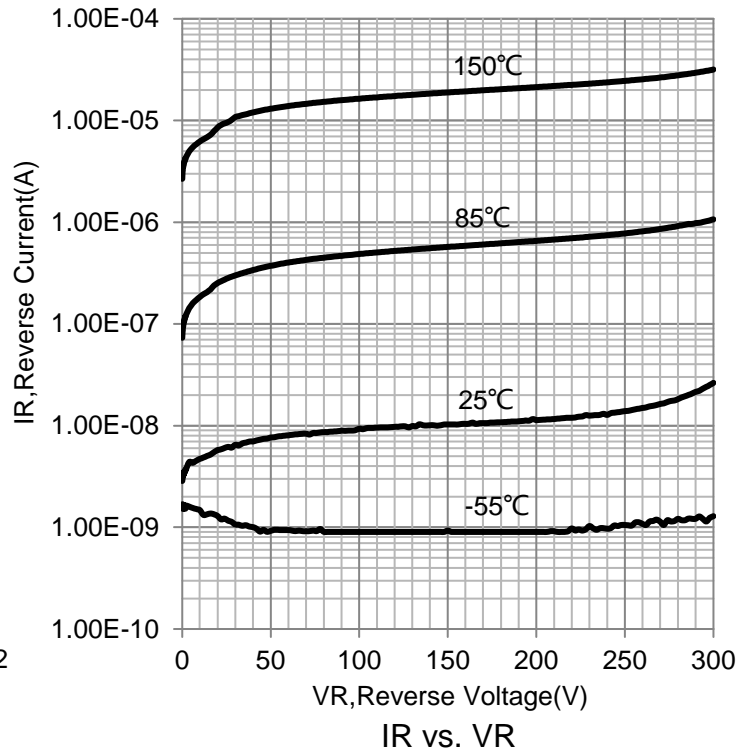
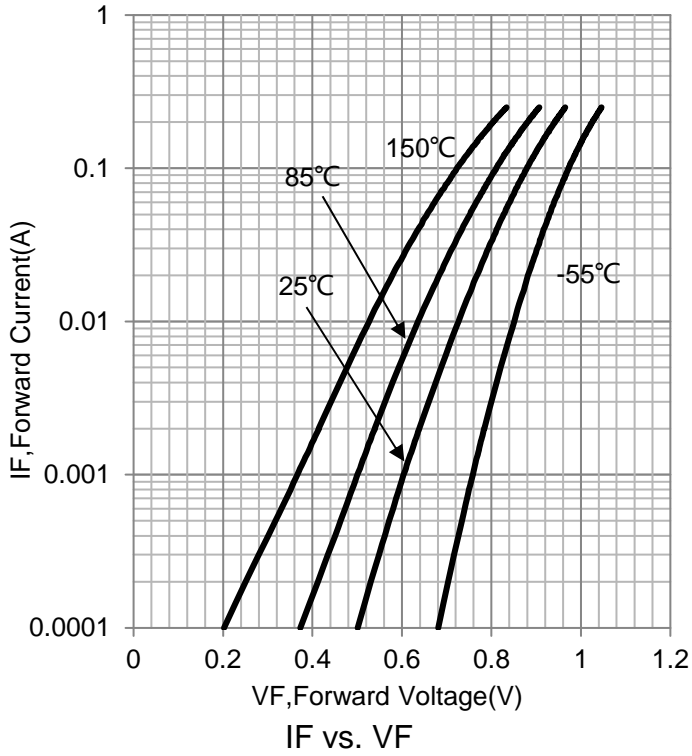
| CHARACTERISTICS | Symbol | Min | Max | Unit |
|---|--------|--------|--------------|------|
| Reverse Voltage Leakage Current (VR=200V) (VR=200V, TJ = 150°C) | IR | - - | 0.1 100 | μA |
| Reverse Breakdown Voltage (IBR = 100 μA) | VBR | 250 | - | V |
| Forward voltage (IF =100mA) (IF =200mA) | VF | - - | 1000 1250 | mV |
| Diode capacitance (f=1MHz, VR =0) | Cd | - | 5 | pF |
| Reverse Recovery Time (IF = IR = 30mA, RL = 100Ω) | Trr | - | 50 | nS |



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

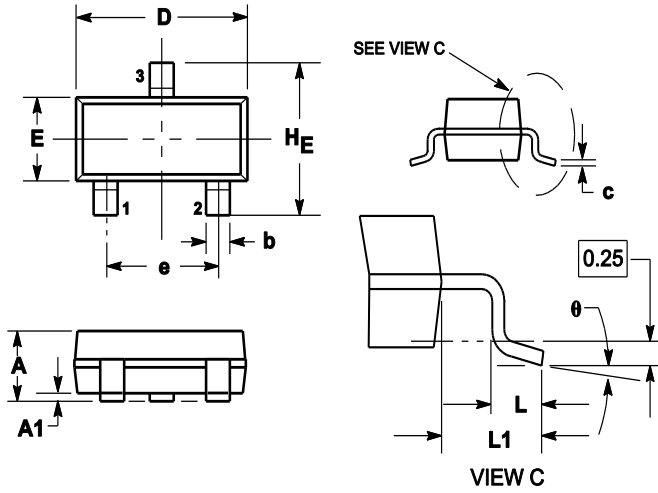
6. ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

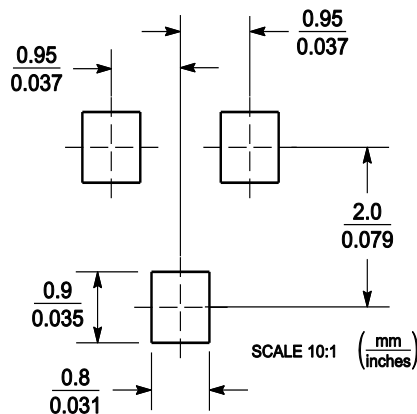
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS | | | INCHES | | |
|-------|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1 | 1.11 | 0.035 | 0.04 | 0.044 |
| A1 | 0.01 | 0.06 | 0.1 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.5 | 0.015 | 0.018 | 0.02 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.9 | 3.04 | 0.11 | 0.114 | 0.12 |
| E | 1.20 | 1.3 | 1.4 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.9 | 2.04 | 0.07 | 0.075 | 0.081 |
| L | 0.10 | 0.2 | 0.3 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.4 | 2.64 | 0.083 | 0.094 | 0.104 |
| theta | 0° | --- | 10° | 0° | --- | 10° |

8. SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)